ATTORNEY DOCKET NO. 10030753-01

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Inventor(s): Laura Wills Mirkarimi Serial No.: 10/765647

Examiner: Duy Vu Nguyen Deo

Filing Date: Jan 26, 2004

Group Art Unit: 1765

Title: Method For Etching High Aspect Ratio Features in III-V Based Compounds For Optoelectrono

Devices

COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:	
This In	formation Disclosure Statement is submitted:
(a) 🗖	Under 37 CFR 1.97(b). (Within three months of filling national application; or date of entry of national application; or before mailing date of first Office action on the ments; whichever occurs last).
(b) 🗷	Under 37 CFR 1.97(c) together with <i>either</i> a: Statement under CFR 1.97(e), or \$180.00 fee under 37 CFR 1.17(p). (After the CFR 1.97(b) time period, but before a final action or notice of allowance, whichever occurs tiret).
(6) □	Under 37 CFR 1.97(d) together with: a Statement under 37 CFR 1.97(e), and \$180.00 fee as set forth in 37 CFR 1.17(p). (After a final action or notice of allowance, whichever occurs first, but before payment of the issue fee).
The ur commuthe filir from a making	TATEMENT UNDER 37 CFR 1.97(e) Indersigned certifies that: ☑ Each item of information contained in the Information Disclosure Statement was first cited in a unication from a foreign patent office in a counterpart foreign application not more than three months prior to any of the statement, or ☑ No item of information contained in the Information Disclosure Statement was cited in a communication foreign patent office in a counterpart foreign application, and, to the knowledge of the undersigned after greasonable inquiry, was known to any individual designated in 37 CFR § 1.56(c) more than three months of the Information Disclosure Statement.
☐ <u>P</u> ! Refere	RIOR APPLICATIONS ences identified with an asterisk (*) in the enclosed PTO Form 1449, were disclosed in prior Patent ation No. , filed , now U.S. Patent No. , and, as such, copies f are not included pursuant to the provisions of 37 CFR 1.98(d).
other foreign	OREIGN LANGUAGE DOCUMENTS A concise explanation of the relevance of foreign language patents, foreign language publications and foreign language information listed on PTO form 1449, as presently understood by the individual(s) nated in 37 CFR 1.56(c) most knowledgeable about the content is given on the attached sheet, or where a nanguage patent is cited in a search report or other action by a foreign patent office in a counterpart foreign atton, an English language version of the search report or action which indicates the degree of relevance by the foreign office is listed on form PTO 1449 and is enclosed herewith.

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FEE AUTHORIZATION Please charge to Deposit Account 50-1078 the sum of this application, please charge any fees required or credit a pursuant to 37 CFR 1.25.	of \$0.00
I hereby certify that this correspondence is being deposited with the United States Postal Service as: First Class Mail 'Express Mail Post office to Addressee' service under 37 CFR 1.10. Express Mai Label No. Date of Deposit: In an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria VA 22313-1450. OR I hereby certify that this paper is being facsimile transmitted to the Patent and Tradement Office on the date shown below. Date of Facsimile: March 29, 2006 Typed Name: Linda A. timura Signature:	Respectfully submitted, Laura Wills Mirkarim By Juerpen Krause-Polstorff Attorney/Agent for Applicant(s) Reg. No. 41,127 Date: March 29, 2006 Telephone No. 650 485-5904

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